



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Up To 3KV
- Lead Free By Design/RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

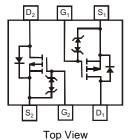
- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

SOT563









Top View

Bottom View

Ordering Information (Note 3)

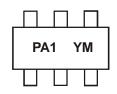
Part Number	Case	Packaging
DMG1023UV-7	SOT563	3,000 / Tape & Reel
DMG1023UV-13	SOT563	10,000 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.

2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



PA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	20	10	2011	2012	2013	2014	. 20	15	2016	2017
Code	V	W)	Κ	Υ	Z	Α	В	(D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

April 2015 © Diodes Incorporated



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	-20	V		
Gate-Source Voltage	V_{GSS}	±6	V		
Continuous Drain Current (Note 4) V _{GS} = -4.5V	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I _D	-1.03 -0.68	Α
Pulsed Drain Current (Note 5)	I _{DM}	-3	Α		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_{D}	530	mW
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 4)	R _{0JA}	235	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

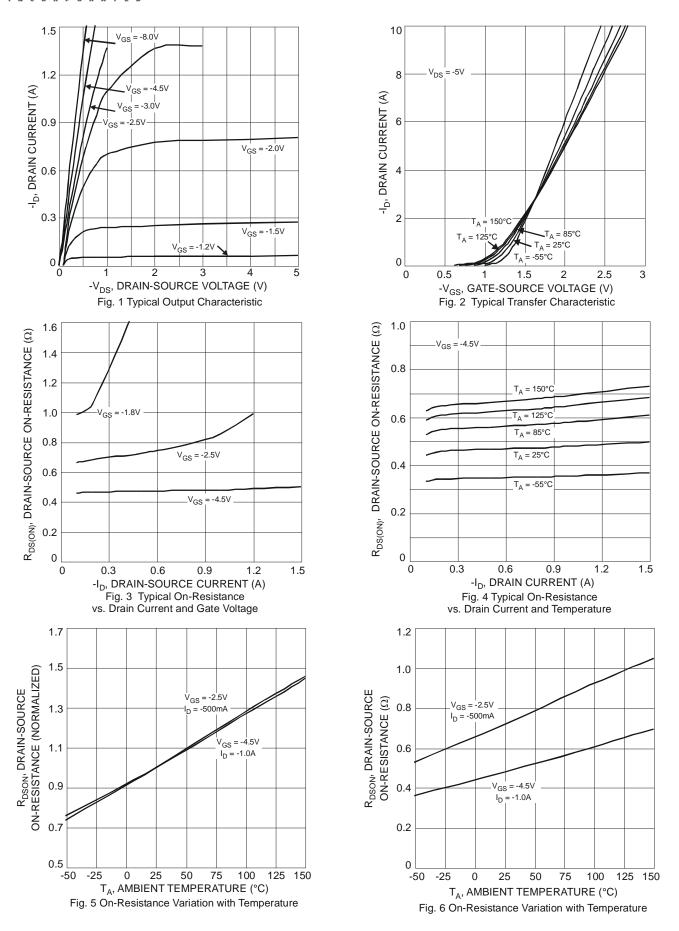
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Tym	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)	Symbol	IVIIII	Тур	IVIAX	Unit	rest Condition
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	_	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage		_	_	±2.0	μA	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)	I _{GSS}			±2.0	μΛ	VGS = ±4.5V, VDS = 0V
Gate Threshold Voltage	V _{GS(th)}	-0.5	l -	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Cate Thiodheld Voltage	V G3(III)	0.0	0.5	0.75	•	$V_{GS} = -4.5V$, $I_D = -430mA$
			0.7	1.05		$V_{GS} = -2.5V$, $I_D = -300$ mA
Static Drain-Source On-Resistance	P== (=+)	-	1.0	1.5	Ω	$V_{GS} = -1.8V$, $I_D = -150$ mA
Static Dialit-Source Off-Nesistance	R _{DS} (ON)		1.0	20		, -
			-	25		$V_{GS} = -1.7V, I_D = -100mA$
5 JT (A) W			-	25		$V_{GS} = -1.5V, I_{D} = -100mA$
Forward Transfer Admittance	Y _{fs}	-	0.9	-	S	$V_{DS} = -10V, I_{D} = -250mA$
Diode Forward Voltage	V_{SD}		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	59.76	-	pF	101/1/
Output Capacitance	Coss	-	12.07	-	pF	$V_{DS} = -16V, V_{GS} = 0V,$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	-	6.36	-	pF	1 = 1:0\vii 12
Total Gate Charge	Qq	-	622.4	-	рC	151/1/ 401/
Gate-Source Charge	Qgs	-	100.3	-	рС	$V_{GS} = -4.5V, V_{DS} = -10V,$
Gate-Drain Charge	Q _{qd}	-	132.2	-	рС	$I_D = -250 \text{mA}$
Turn-On Delay Time	t _{D(on)}	-	5.1	-	ns	
Turn-On Rise Time	t _r	-	8.1	-	ns	V _{DD} = -10V, V _{GS} = -4.5V,
Turn-Off Delay Time	t _{D(off)}	-	28.4	-	ns	$R_L = 47\Omega, R_G = 10\Omega,$ $R_D = -200 \text{mA}$
Turn-Off Fall Time	t _f	-	20.7	-	ns	200ΠΑ

Notes:

- 4. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 5. Repetitive rating, pulse width limited by junction temperature.6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to production testing.







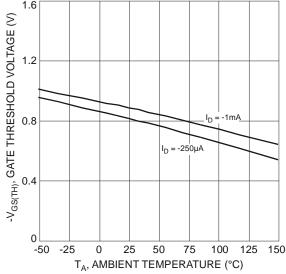
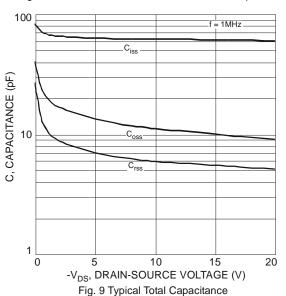
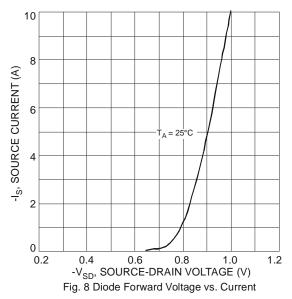


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





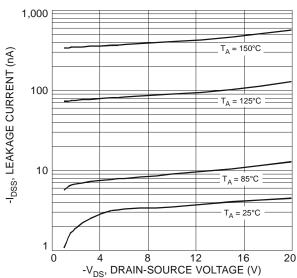


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

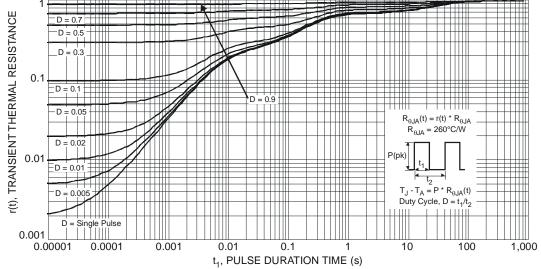
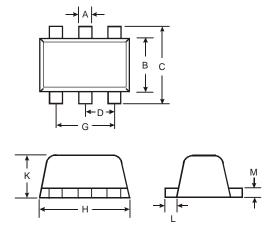


Fig. 11 Transient Thermal Response

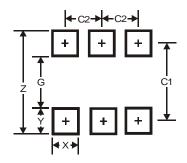


Package Outline Dimensions



SOT563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
M	0.10	0.18	0.11				
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)			
Z	2.2			
G	1.2			
Х	0.375			
Y	0.5			
C1	1.7			
C2	0.5			



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND. EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT. INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSÉ (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2012, Diodes Incorporated

www.diodes.com

6 of 6 DMG1023UV April 2015 Document number: DS31975 Rev. 6 - 2 © Diodes Incorporated 单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达尔科技)